

isc Silicon NPN Power Transistor

2SD845

DESCRIPTION

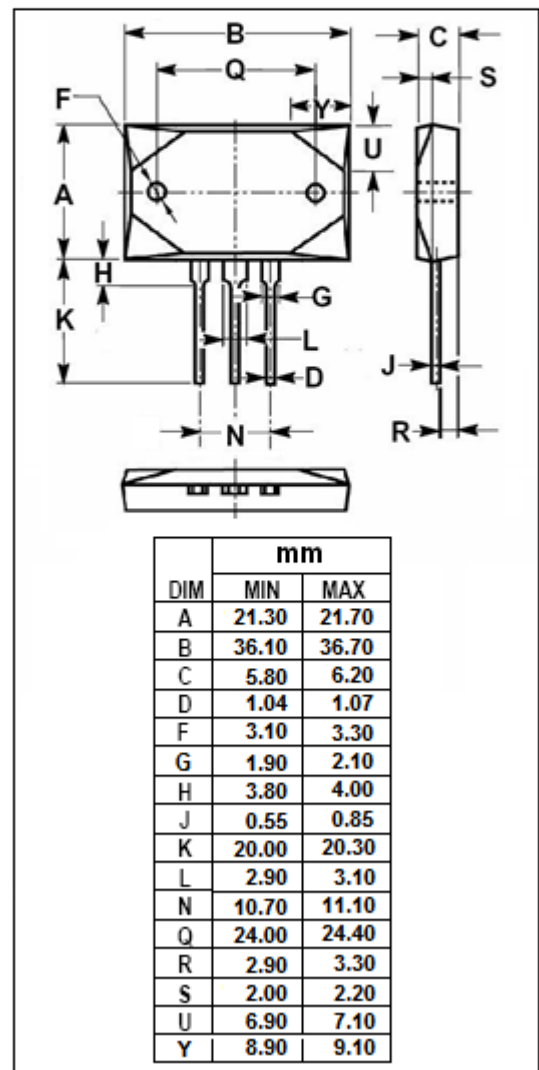
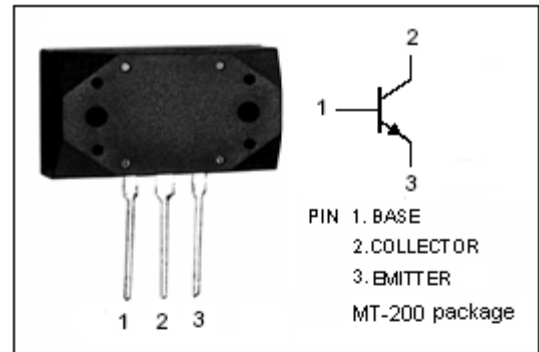
- Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = 150V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SB755

APPLICATIONS

- Designed for power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	12	A
I_E	Emitter Current-Continuous	-12	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	120	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SD845****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=0.1\text{A}; I_B=0$	150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\text{mA}; I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=5\text{A}; V_{CE}=5\text{V}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=150\text{V}; I_E=0$			50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			50	μA
h_{FE}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	55		160	
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1.0\text{MHz}$		200		pF
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}; V_{CE}=10\text{V}$		20		MHz

◆ **h_{FE} Classifications**

R	O
55-110	80-160